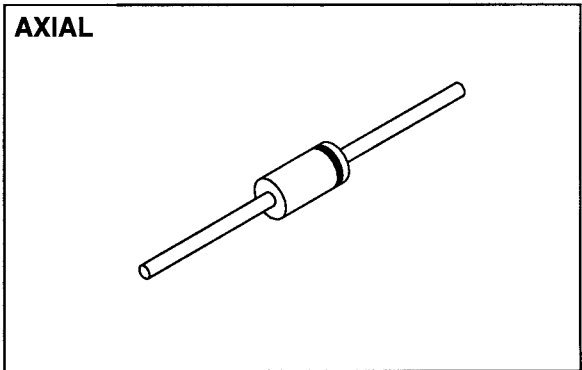


**SPD0801
 thru
 SPD1001**

Designer's Data Sheet

- FEATURES:**
- PIV to 100 Volts
 - Extremely Low Forward Voltage Drop
 - Low Reverse Leakage Current
 - High Surge Capacity
 - High Voltage Replacement for:
 - 1N5817-1N5819 Series
 - Surface mount versions available
 - TX, TXV and Space Level Screening Available

**1 AMP
 80-100 VOLTS
 SCHOTTKY
 RECTIFIER**



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage SPD0801 SPD0901 SPD1001	VRRM VRWM VR	 80 90 100	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	IO	1	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on IO, allow junction to reach equilibrium between pulses, TA=25°C)	IFSM	40	Amps
Operating and storage temperature	Top & Tstg	-55 to +125	°C
Maximum Thermal Resistance Junction to Lead, L=3/8"	RθJL	46	°C/W

NOTE: All specifications are subject to change without notification. SSD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET#: RS0115 B

RMD

**SPD0801
thru
SPD1001**

PRELIMINARY



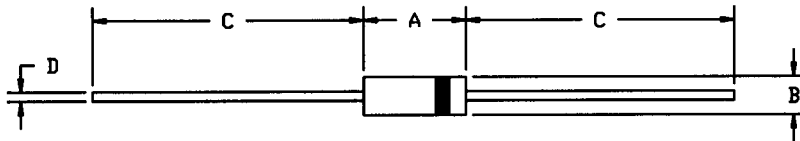
SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop (IF = 0.5 Adc, TA=25°C, 300µs Pulse) (IF = 1 Adc, TA=25°C, 300µs Pulse)	VF	0.75 0.95	Vdc
Instantaneous Forward Voltage Drop (IF = 1 Adc, TA= - 55°C, 300µs Pulse)	VF	1.0	Vdc
Reverse Leakage Current (Rated VR, TA=25°C, 300µs pulse minimum)	IR	200	µA
Reverse Leakage Current (Rated VR, TA=100°C, 300µs pulse minimum)	IR	10	mA
Junction Capacitance (VR = 10 Vdc, TA=25°C, f= 1 MHz)	CJ	30	pf

CASE OUTLINE:



NOTE: Lead diameter is not controlled within .050" of the diode body.

DIMENSIONS		
DIM	MIN.	MAX.
A	.160"	.205"
B	.080"	.107"
C	1.00"	---
D	.028"	.032"

TYPICAL OPERATING CURVES

(TA=25°C unless otherwise specified)

